

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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# 2SK1317

Silicon N-Channel MOS FET

**RENESAS**

ADE-208-1268 (Z)  
1st. Edition  
Mar. 2001

## Application

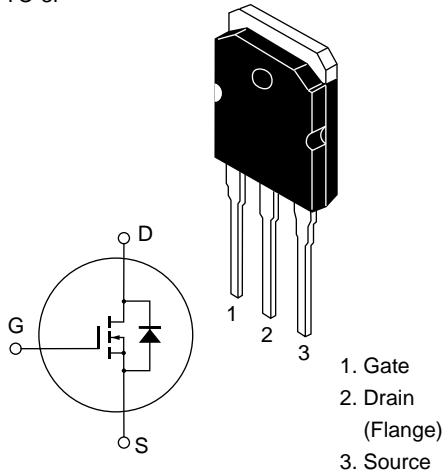
High speed power switching

## Features

- High breakdown voltage  $V_{DSS} = 1500\text{ V}$
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter and motor driver

## Outline

TO-3P



## Absolute Maximum Ratings (Ta = 25°C)

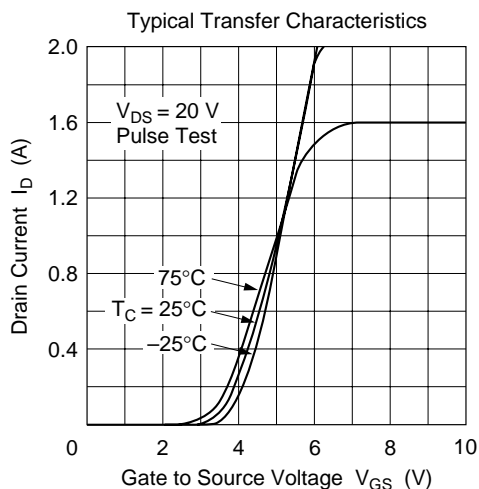
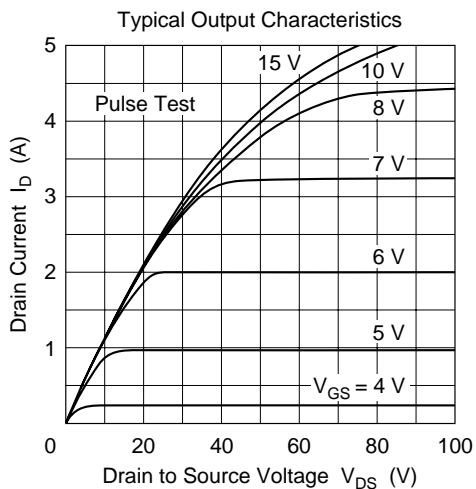
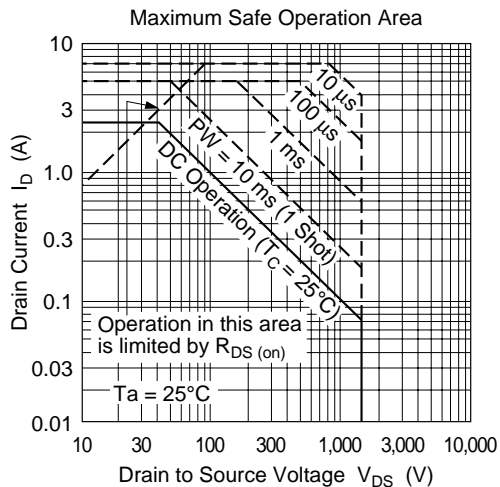
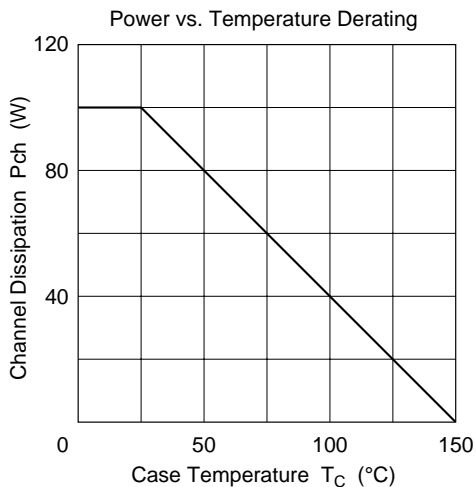
Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	1500	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	2.5	A
Drain peak current	$I_{D(pulse)}^{*1}$	7	A
Body to drain diode reverse drain current	$I_{DR}$	2.5	A
Channel dissipation	$P_{ch}^{*2}$	100	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

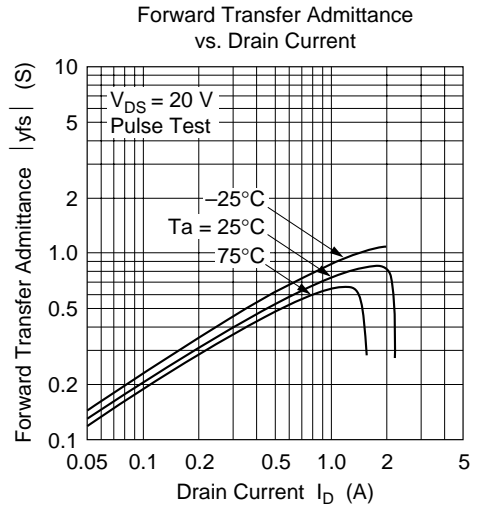
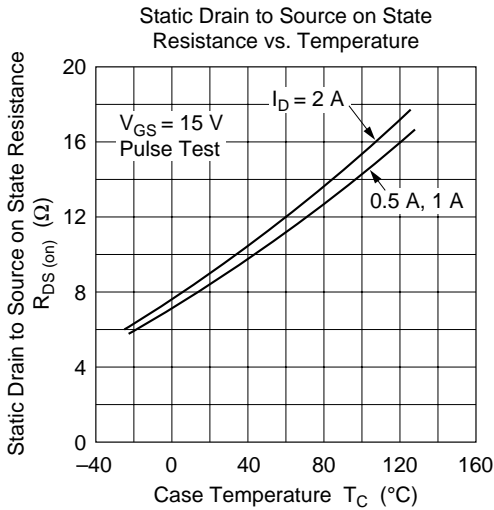
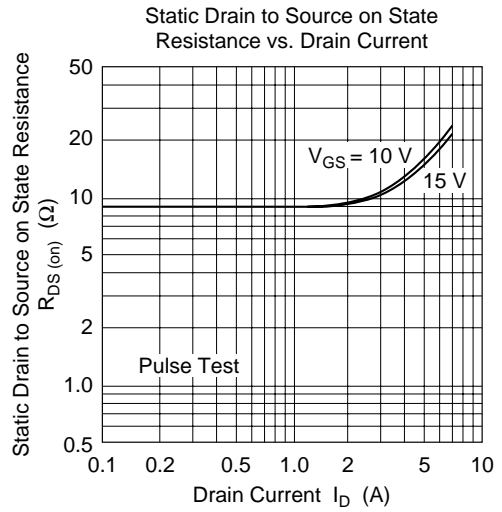
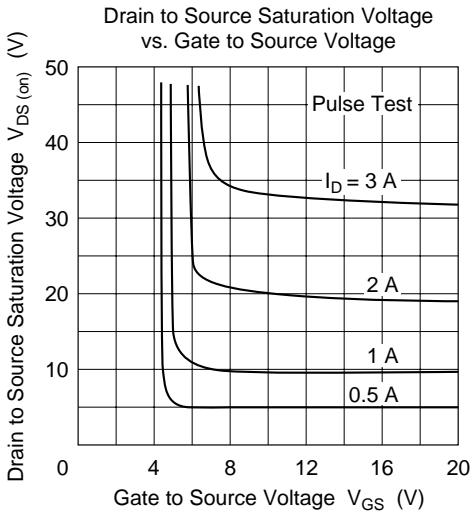
Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$   
 2. Value at  $T_c = 25^\circ C$

## Electrical Characteristics (Ta = 25°C)

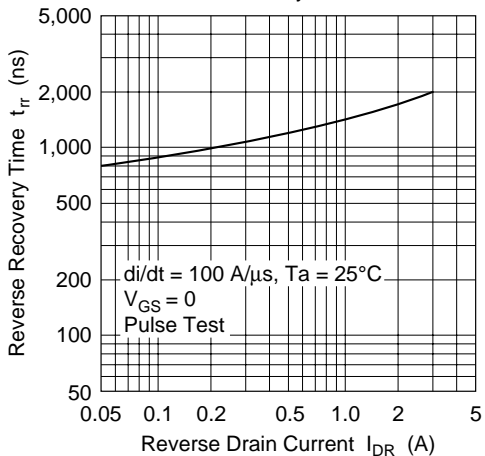
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	1500	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±1	μA	$V_{GS} = \pm 20 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	500	μA	$V_{DS} = 1200 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	4.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	9	12	Ω	$I_D = 2 \text{ A}$ , $V_{GS} = 15 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	0.45	0.75	—	S	$I_D = 1 \text{ A}$ , $V_{DS} = 20 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	990	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ ,
Output capacitance	$C_{oss}$	—	125	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	—	60	—	pF	
Turn-on delay time	$t_{d(on)}$	—	17	—	ns	$I_D = 2 \text{ A}$ , $V_{GS} = 10 \text{ V}$ ,
Rise time	$t_r$	—	70	—	ns	$R_L = 15 \Omega$
Turn-off delay time	$t_{d(off)}$	—	110	—	ns	
Fall time	$t_f$	—	60	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	0.9	—	V	$I_F = 2 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	1750	—	ns	$I_F = 2 \text{ A}$ , $V_{GS} = 0$ , $di_F/dt = 100 \text{ A}/\mu s$

Note: 1. Pulse test

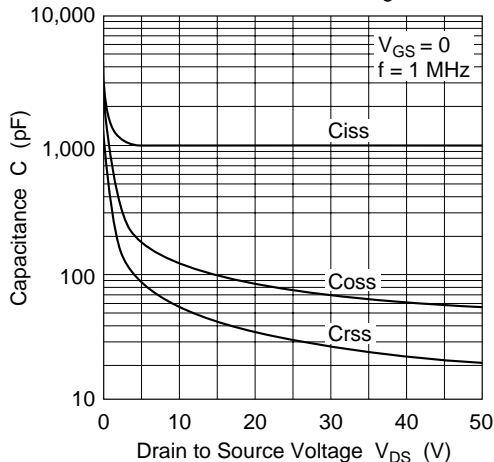




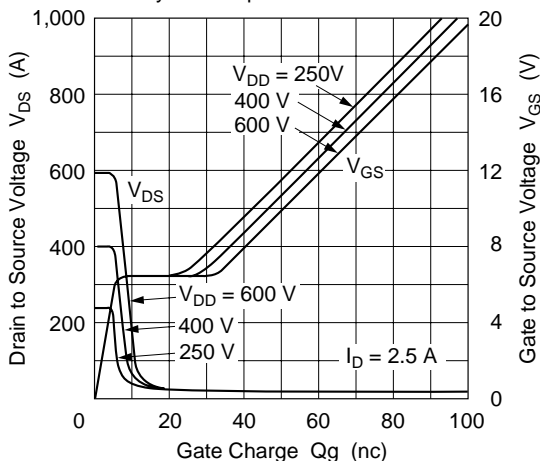
Body to Drain Diode Reverse Recovery Time



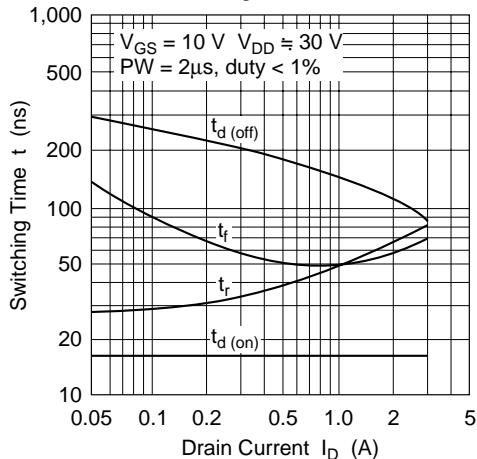
Typical Capacitance vs. Drain to Source Voltage

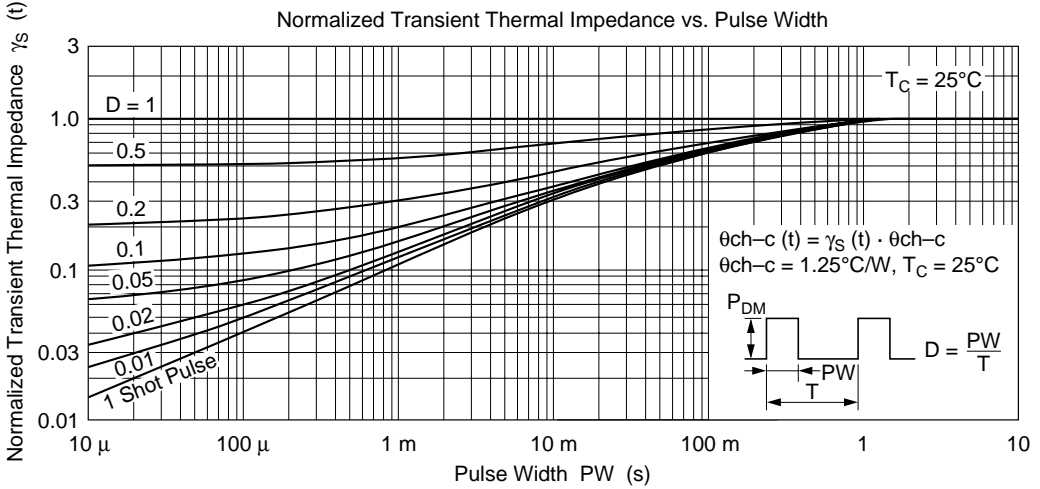
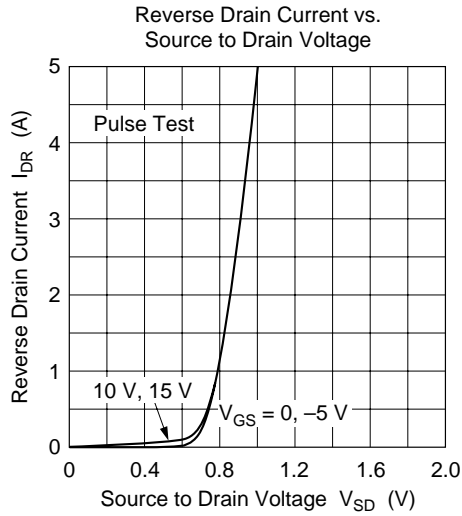


Dynamic Input Characteristics

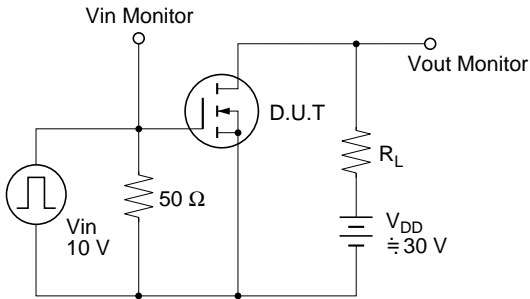


Switching Characteristics

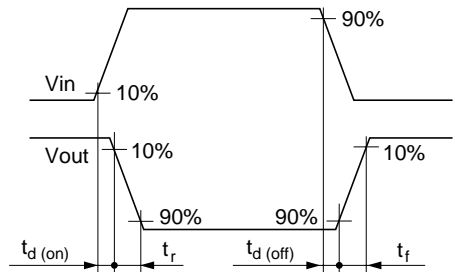




Switching Time Test Circuit



Waveforms

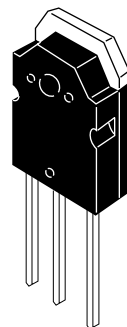
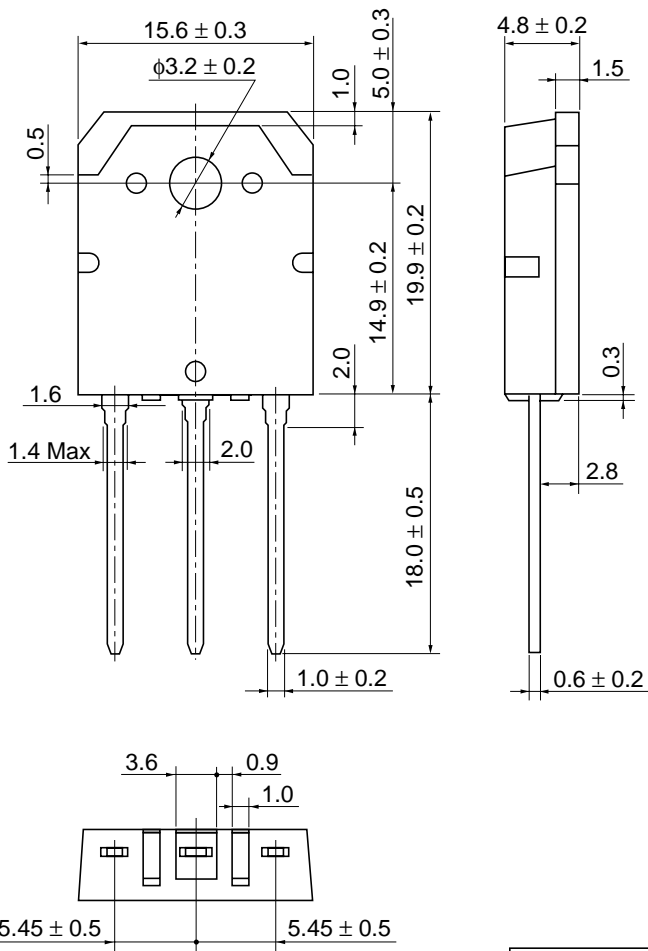




Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

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